Nell High Power Products

FRED
Hyperfast Soft Recovery Diode
100A x 2 / 1200V

Pb Available RoHS* COMPLIANT

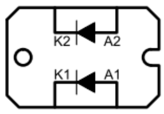
FEATURES

- Hyperfast recovery time characteristic
- Electrically isolated base plate
- Large creepage distance between terminal
- Simplified mechanical designs, rapid assembly
- Compliant to RoHS
- Designed and for industrial level
- Planar passivated chips

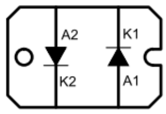
DESCRIPTION

This SOT-227 modules with FRED rectifier are available in two basic configurations. They are the antiparallel and the parallel configurations. The antiparallel configuration NST200HF12-A is used for simple series rectifier and high voltage application. The parallel configuration NST200HF12 is used for simple parallel rectifier and high current application. The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

CIRCUIT CONFIGURATION



Parallel
NST200HF12



Anti-Parallel
NST200HF12-A

APPLICATIONS

- Switching power supplies
- Inverters
- Motor controllers
- Converters
- Snubber diodes
- Uninterruptible power supplies (UPS)
- Induction heating
- High speed rectifiers
- Free wheeling diodes
- Battery chargers
- Welders

PRODUCT SUMMARY	
V_R	1200 V
V_F(typical) at 125 °C	1.90 V
t_{rr} (typical)	50 ns
$I_{F(DC)}$ at T_C per diode	100A at 90 °C

ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Cathode to anode voltage		V_R		1200	V
Maximum continuous forward current	per leg	I_F	T_c = 90 °C	100	A
	per module			200	
Single pulse forward current		I_{FSM}	T_J = 25 °C	1000	
RMS isolation voltage, any terminal to case		V_{ISOL}	t = 1 minute	2500	V
Maximum power dissipation		P_D	T_c = 25 °C	375	W
			T_c = 100 °C	188	
Operating junction and storage temperature range		T_J, T_{Stg}		- 55 to 175	°C

ELECTRICAL SPECIFICATIONS (T_J = 25 ºC unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V_{BR}	I_R = 100 µA	1200	-	-	V
Maximum forward voltage	V_{FM}	I_F = 100 A	-	2.70	3.10	
		I_F = 200 A	-	3.20	-	
		I_F = 100 A, T_J = 125 ºC	-	1.90	-	
Maximum reverse leakage current	I_{RM}	V_R = V_R rated	-	0.5	50	µA
		T_J = 125°C, V_R = V_R rated	-	-	1.0	mA
Junction capacitance	C_J	V_R = 200V		120		pF

DYNAMIC RECOVERY CHARACTERISTICS PER LEG (T_J = 25 ºC unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time	t_{rr}	I_F = 0.5A, I_R = 1.0A, I_{RR} = 250mA (RG#1 CKT)		-	85	110	ns
		I_F = 1.0 A, dI_F/dt = -100 A/µs, V_R =30 V, T_J = 25°C		-	50	-	
	t_{rr1}	T_J = 25 ºC	I_F= 100A, dI_F/dt = -200 A/µs, V_R =800 V	-	380	-	
	t_{rr2}	T_J = 125 ºC		-	490	-	
Reverse recovery current	I_{RRM1}	T_J = 25 ºC		-	6	-	A
	I_{RRM2}	T_J = 125 ºC		-	19	-	
Reverse recovery charge	Q_{rr1}	T_J = 25 ºC		-	1140	-	nC
	Q_{rr2}	T_J = 125 ºC		-	4655	-	

THERMAL - MECHANICAL SPECIFICATIONS (T_J = 25 ºC unless otherwise specified)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS
Junction to case, single leg conducting	R_{thJC}	-	-	0.40	ºC/W K/W
Junction to case, both legs conducting		-	-	0.20	
Case to sink, flat, greased surface	R_{thCS}	-	0.05	-	
Weight		-	30	-	g
Mounting torque		-	-	1.1	Nm

Fig.1 Maximum effective transient thermal impedance, junction-to-case vs. pulse duration

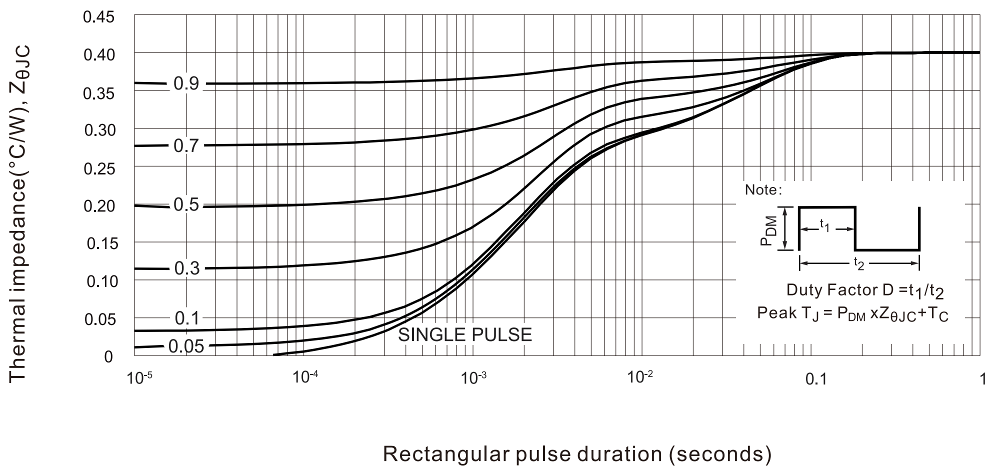


Fig.2 Forward current vs. forward voltage

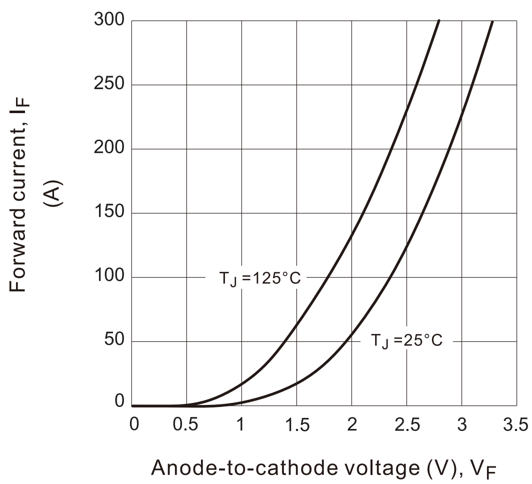


Fig.3 Reverse recovery time vs. current rate of change

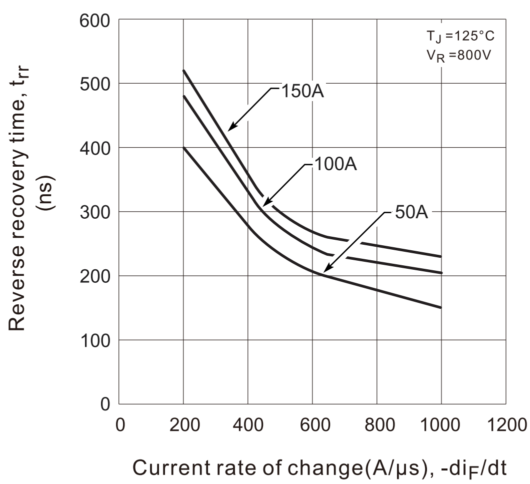


Fig.4 Reverse recovery charge vs. current rate of change

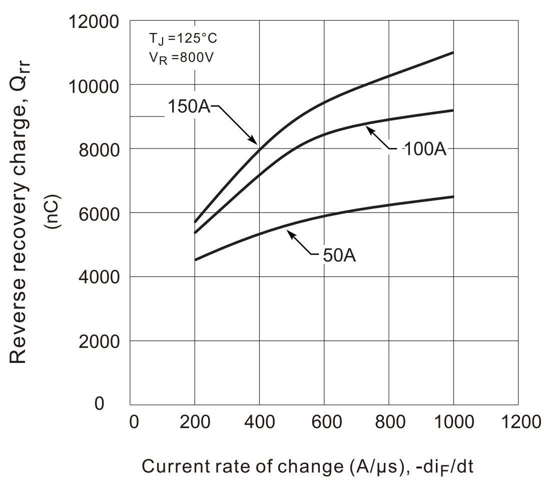


Fig 5. Reverse recovery current vs. current rate of change

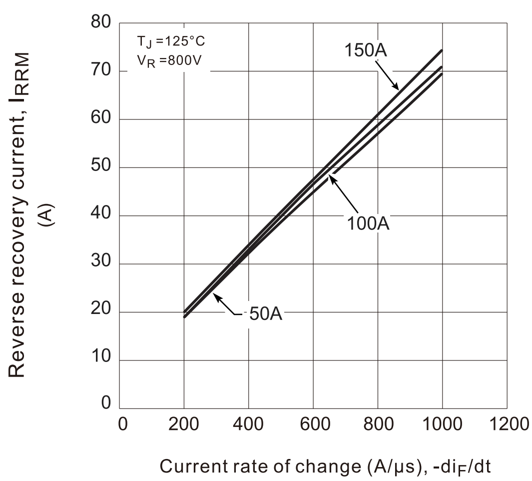


Fig6. Dynamic parameters vs. junction temperature

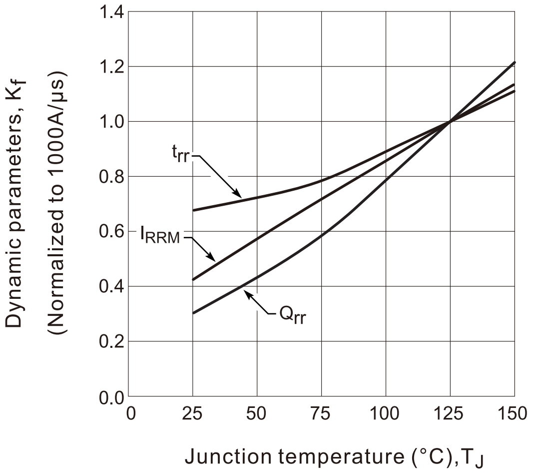


Fig.7 Maximum average forward current vs. case temperature

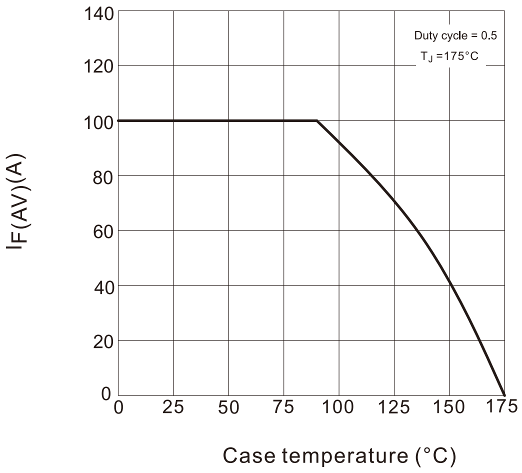


Fig.8 Junction capacitance vs. reverse voltage

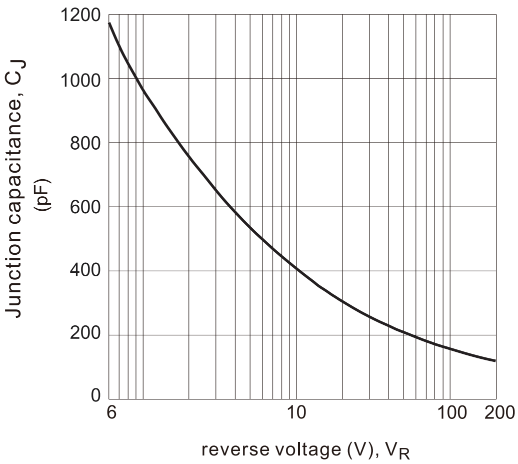


Fig.9 Reverse recovery parameter test circuit

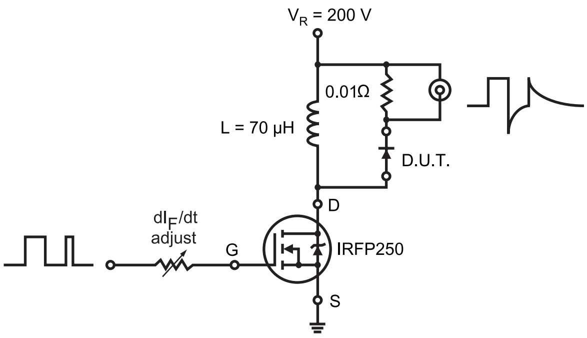
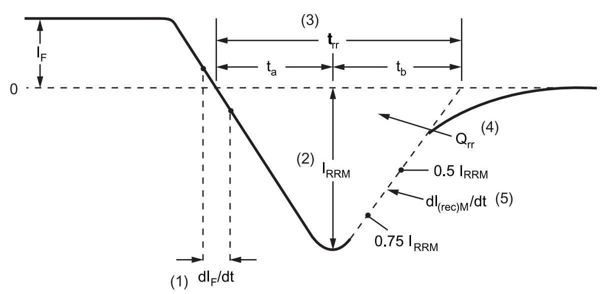


Fig.10 Reverse recovery waveform and definitions



(1) dI_F/dt - rate of change of current through zero crossing

(2) I_{RRM} - peak reverse recovery current

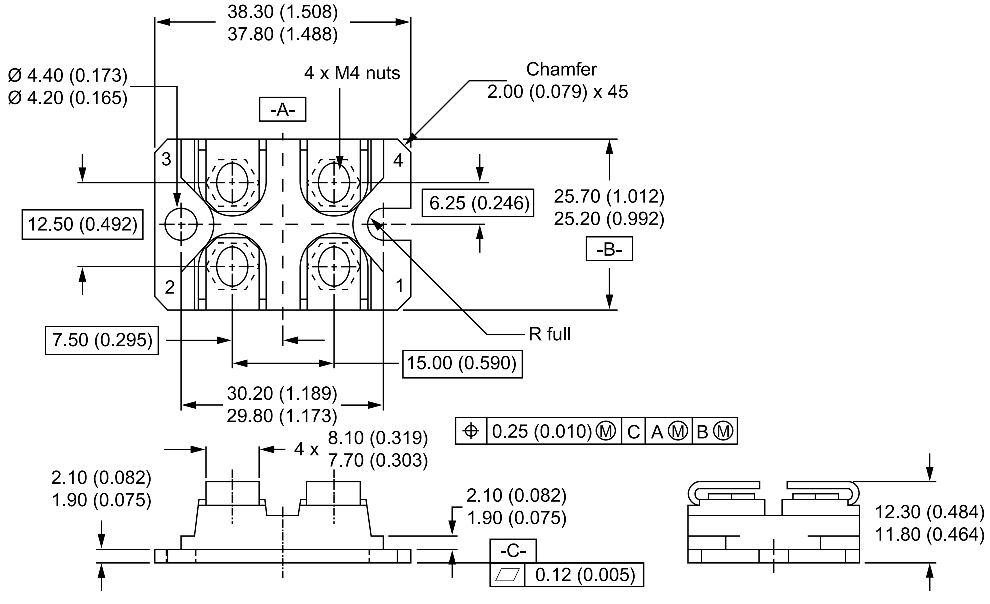
(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} x I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

SOT-227



All dimensions in millimeters (inches)

Notes

- Dimensioning and toleranc ing per ANSI Y14.5M-1982
- Controlling dime nsion: millimeter

ORDERING INFORMATION TABLE

Device code	N	ST	200	HF	12	–	A
	1	2	3	4	5		6

1 - Nell High Power Products

2 - Package indicator (SOT-227)

3 - Current rating (200 = 200A, 100A x 2)

4 - HF = FRED family, planar passivated hyperfast soft recovery chips

5 - Voltage rating (12 = 1200 V)

6 - Circuit type, A for Anti-Parallel type
Blank for parallel type.